



Electronic Properties of Metal Halide Perovskites and their Interfaces with Charge Extraction Layers in Lateral Heterojunction Configuration

Sean P. Dunfield, Aleksandra Bojar, Stefania Cacovich, Mathieu Frégnaux, Talysa Klein, Rosemary Bramante, Fei Zhang, Davide Regaldo, Vincent Dufoulon, Jean-Baptiste Puel, et al.

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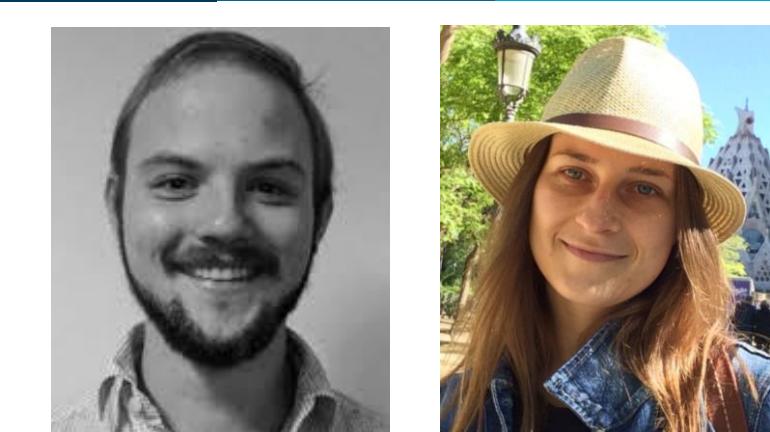
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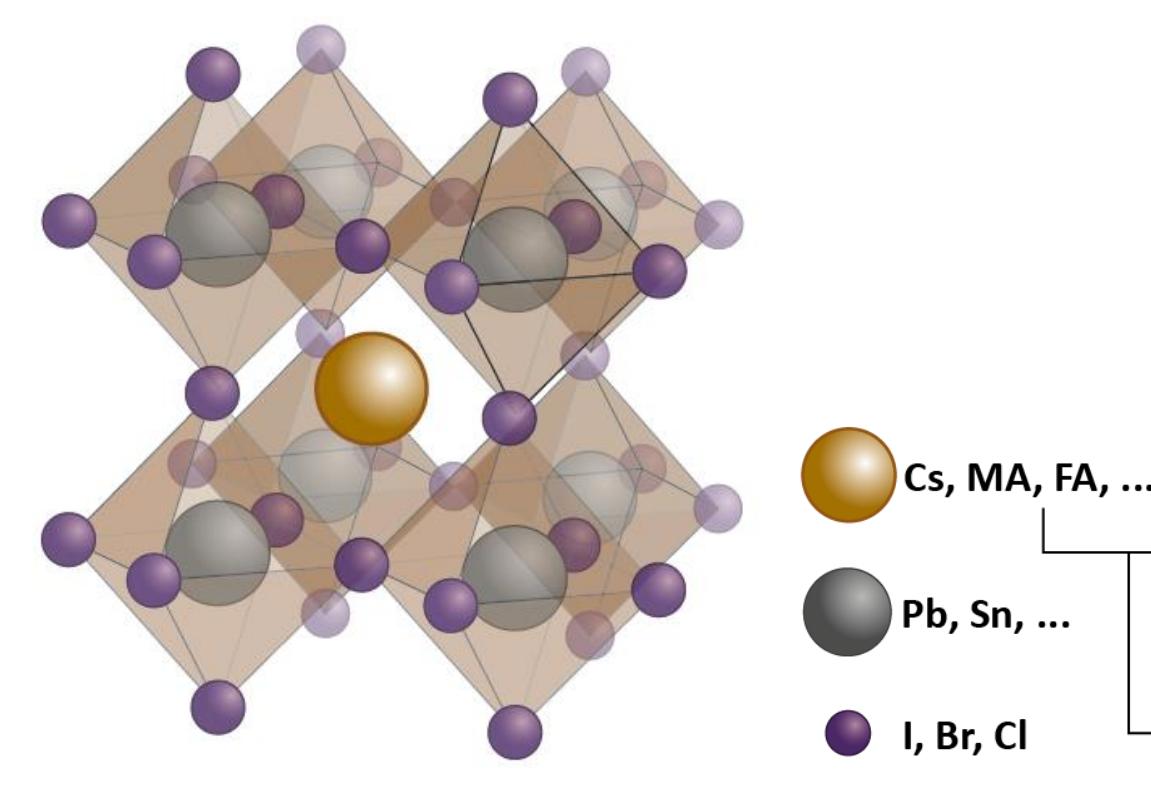
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Electronic Properties of Metal Halide Perovskites and their Interfaces with Charge Extraction Layers in Lateral Heterojunction Configuration

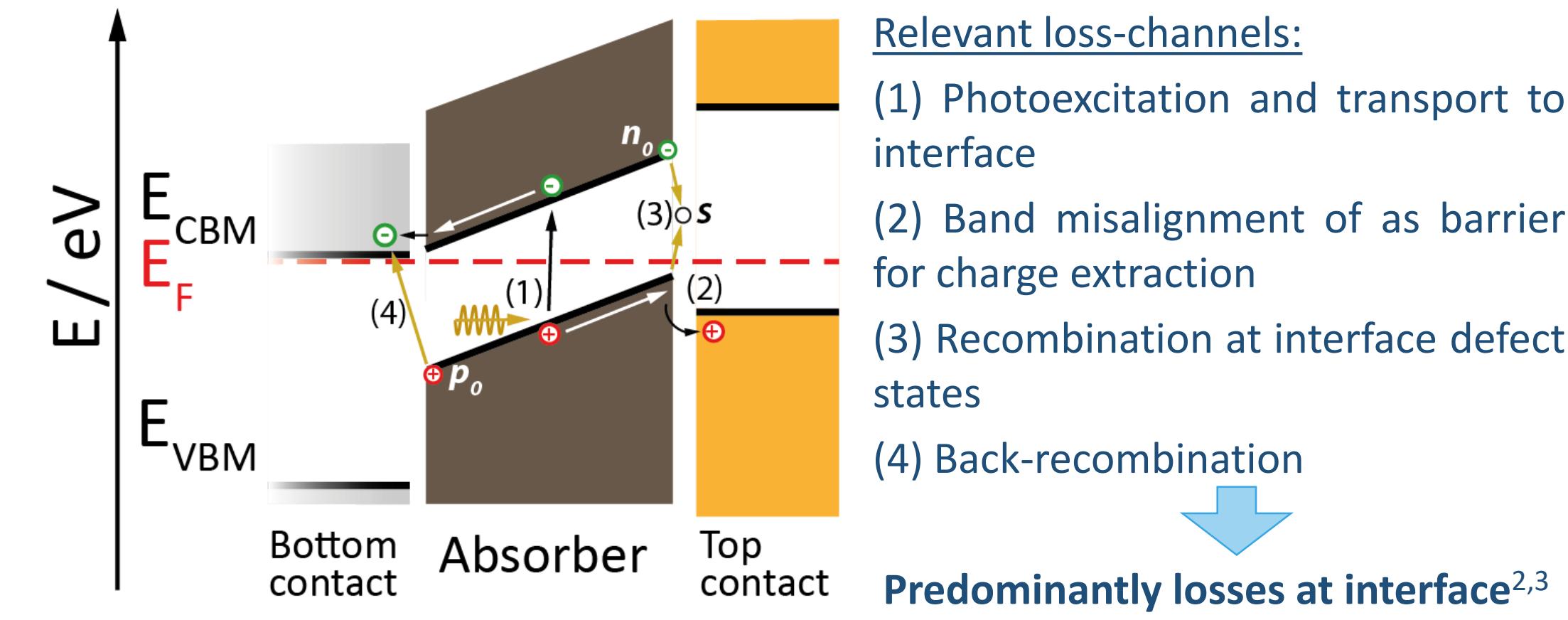
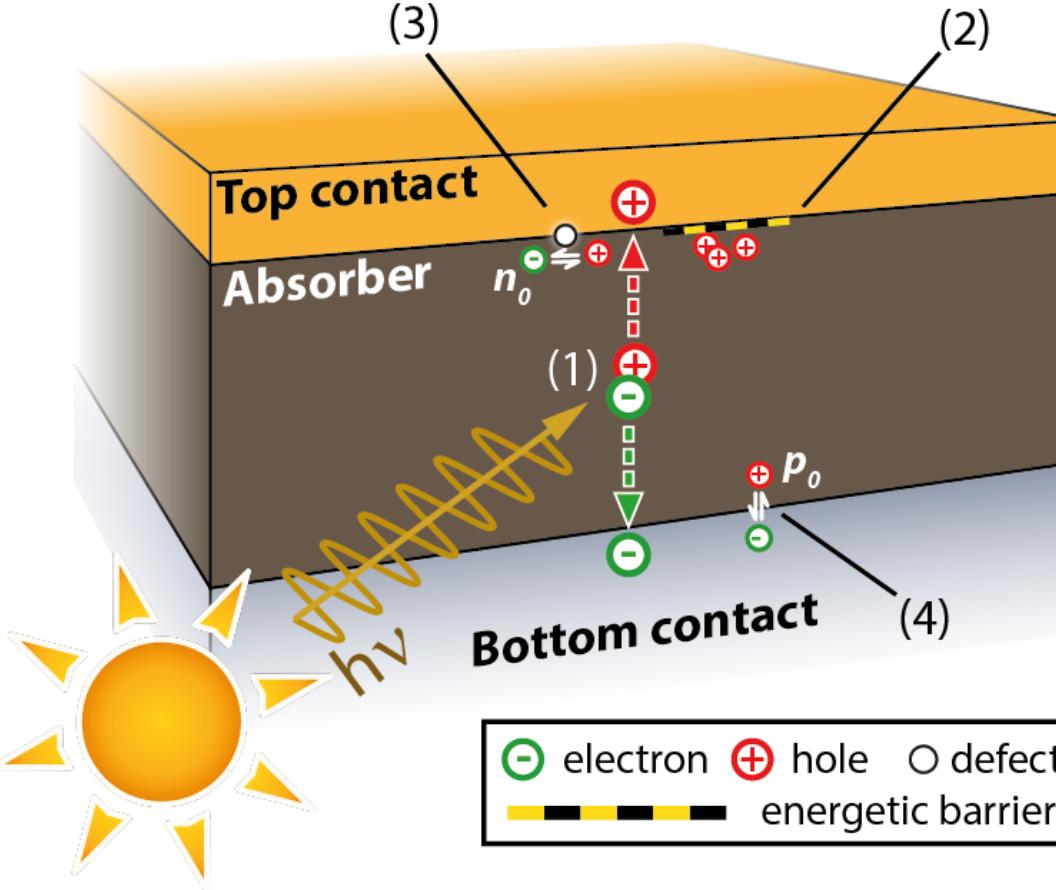
Metal Halide Perovskites: Applications and Interfaces



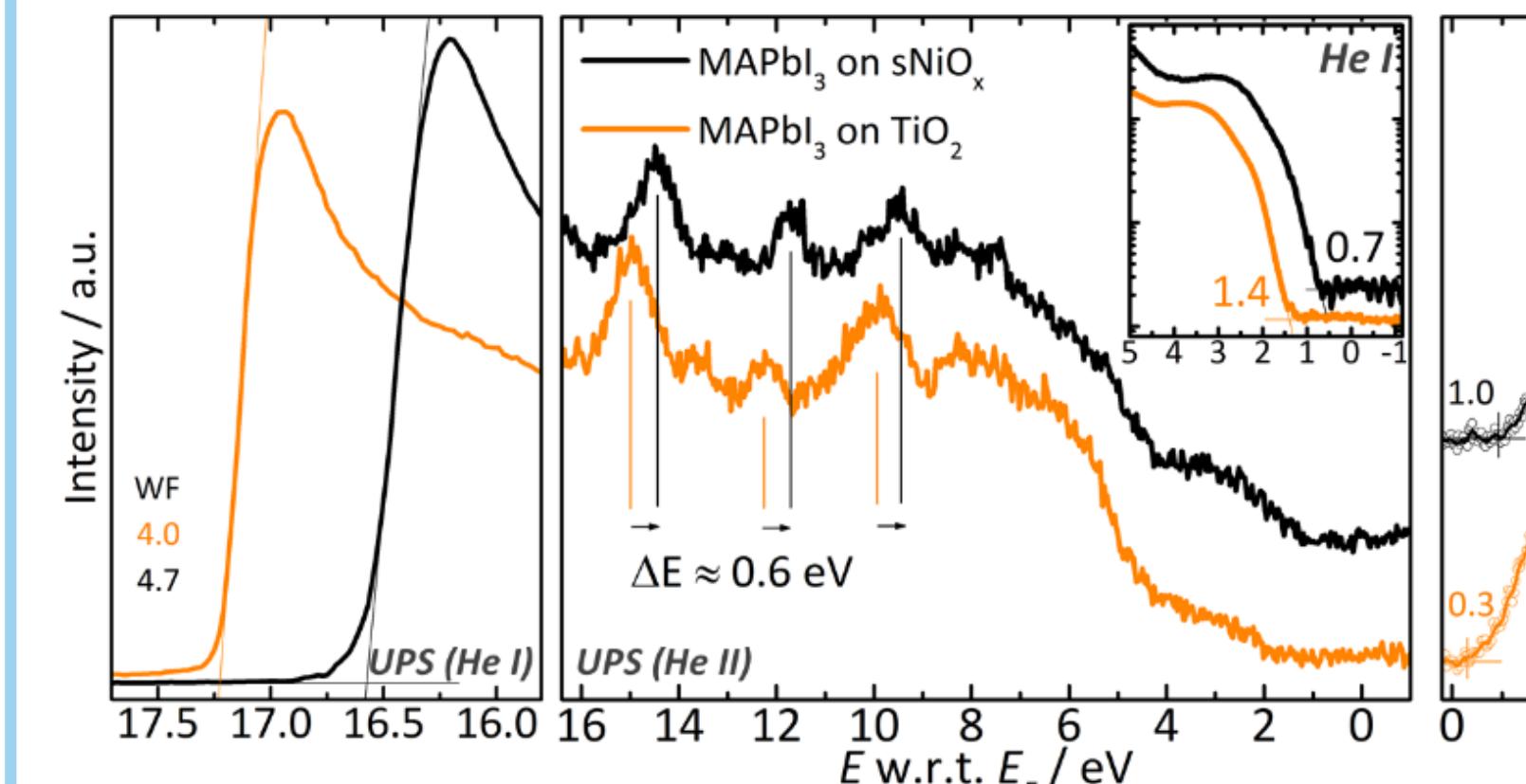
Hybrid organic-inorganic metal halide perovskite (MHP) with complex chemical structure ABX_3

Semiconductor with unique combination of optoelectronic and mechanical properties¹

Breakthrough application in photovoltaics: Perovskite solar cells (PSC)



Substrate-dependent Fermi Level Alignment and Lateral Heterojunction (LHJ)

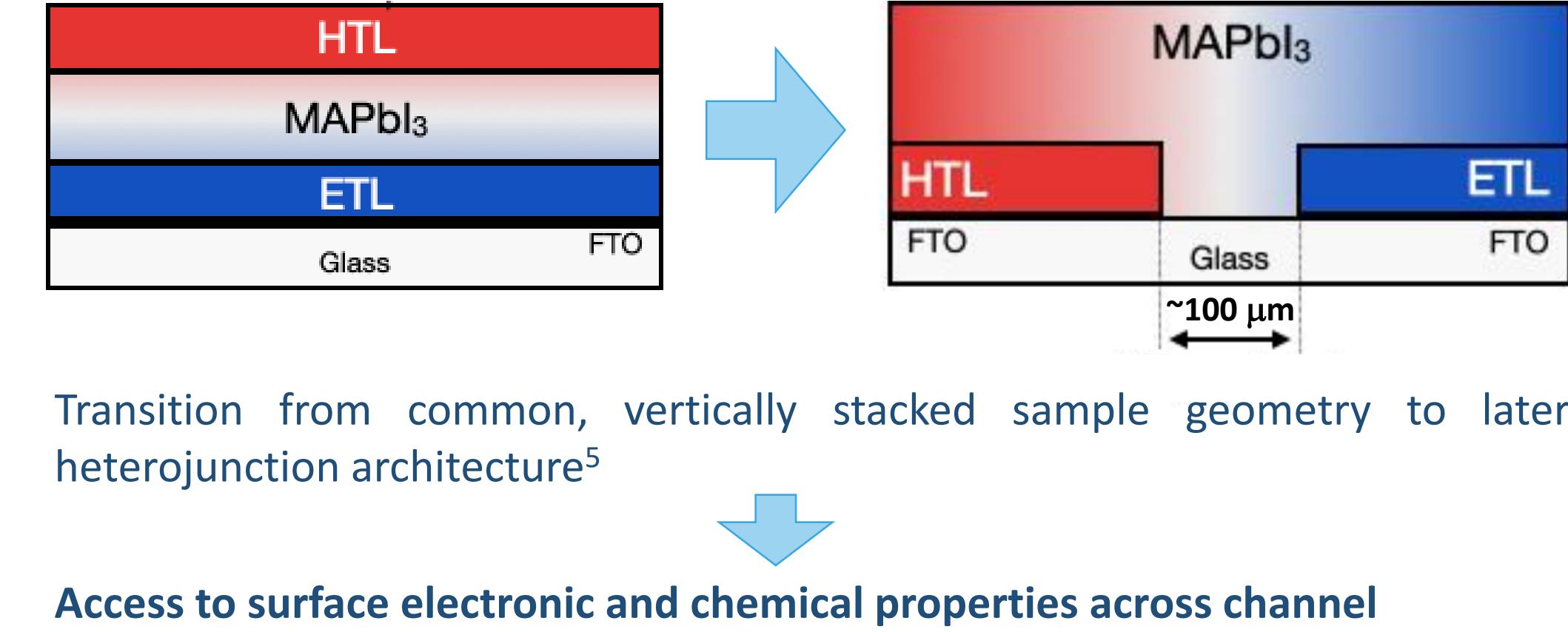


Combined ultraviolet and inverse photoemission spectroscopy (UPS/IPES)⁴:

Optoelectronic properties of MHP can be altered by the substrate (or selective contact) underneath

Position of Fermi level (E_F) at the surface of the perovskite film (MAPbI₃, 400 nm) changes on different substrate, with E_F close to the perovskite conduction band on TiO₂ and in a mid-gap position on NiO

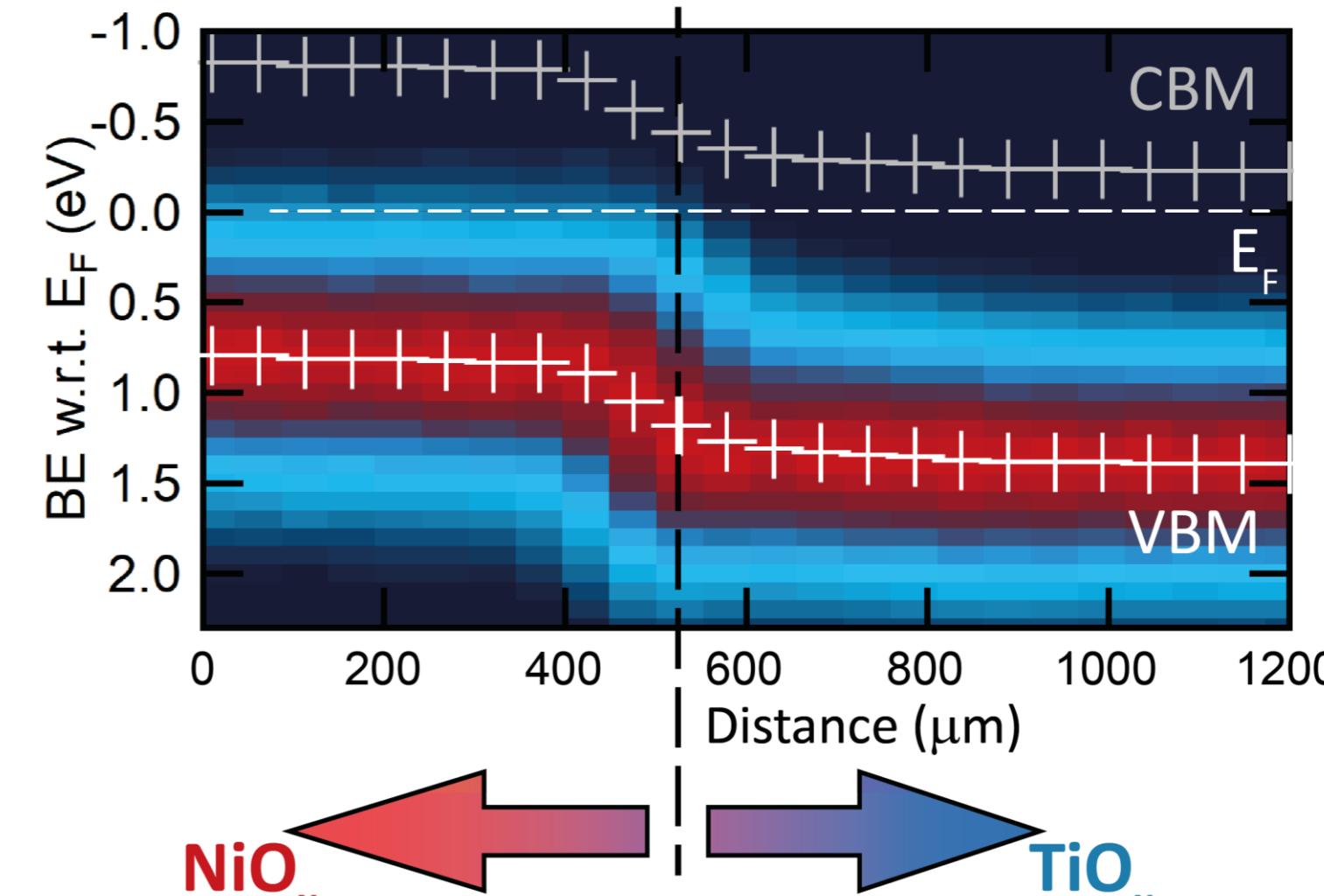
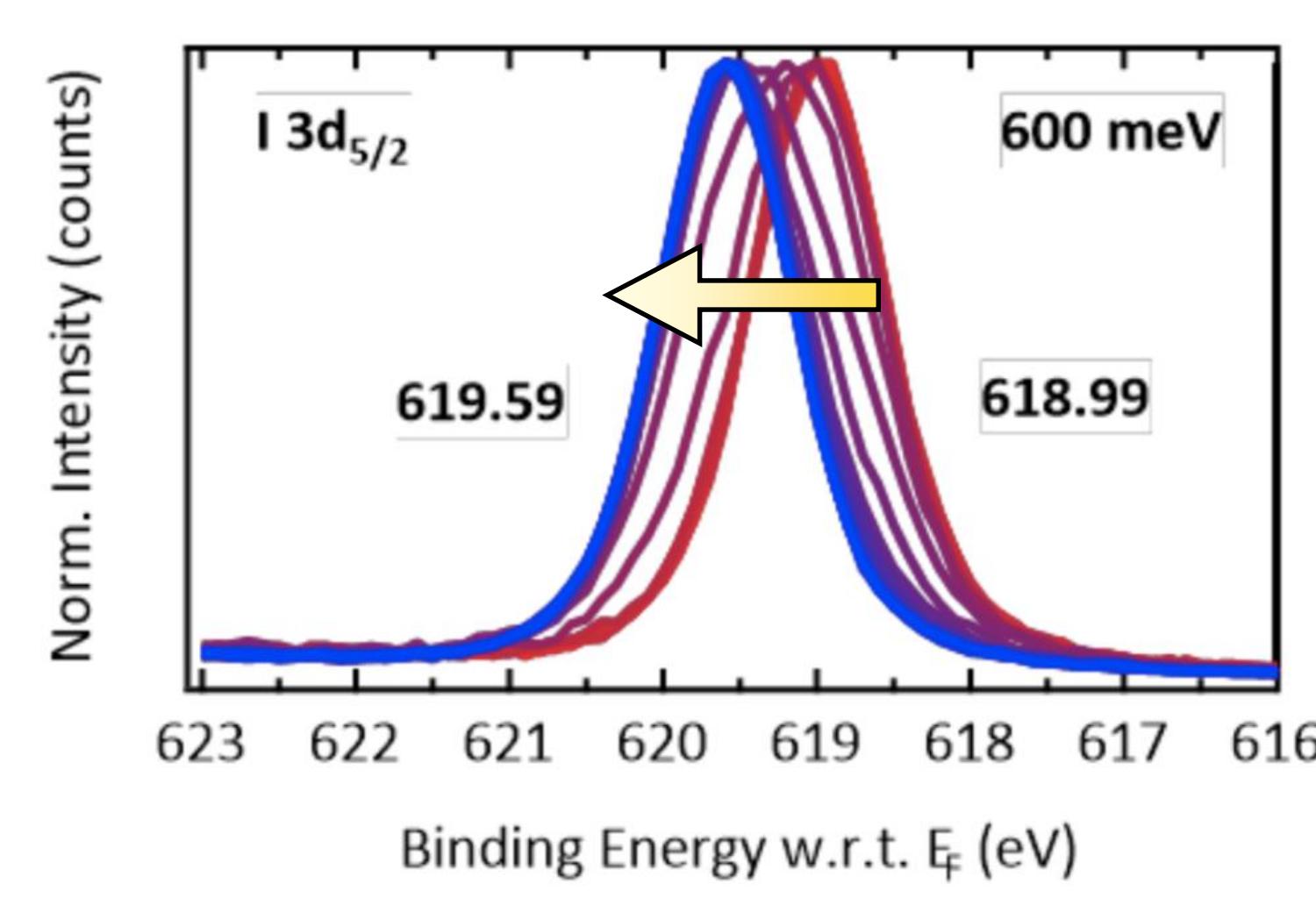
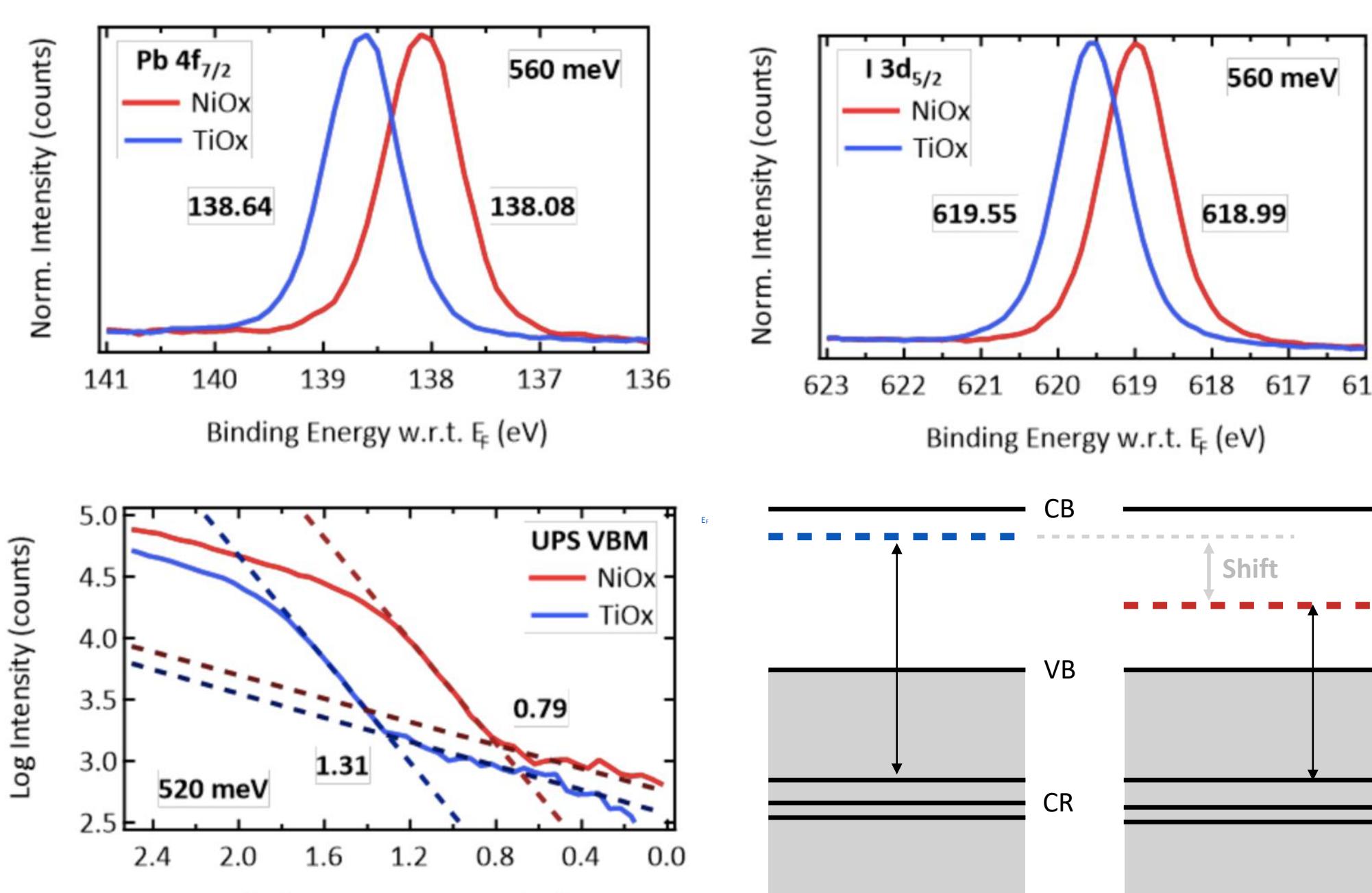
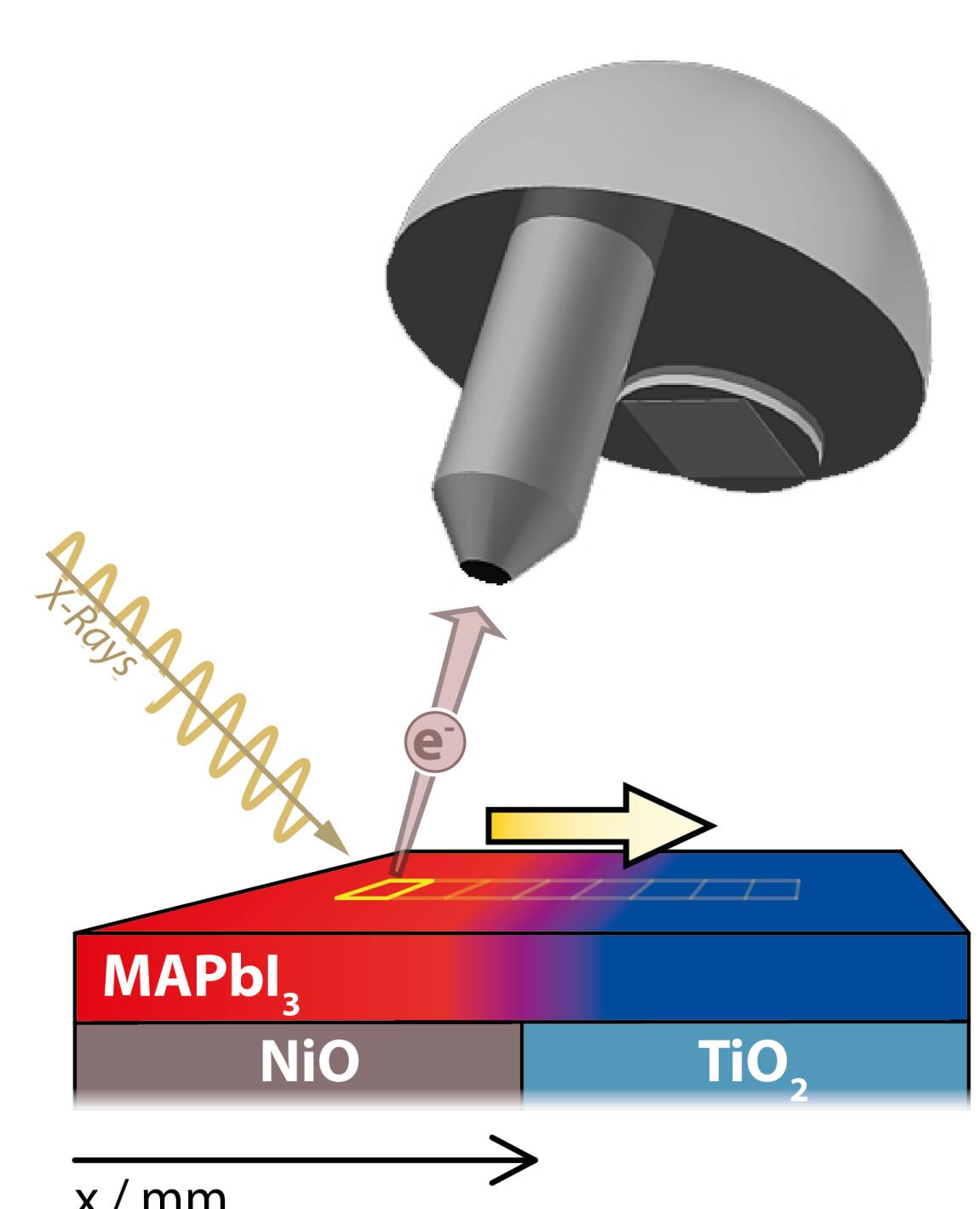
Need to track interface formation and energy level alignment



Transition from common, vertically stacked sample geometry to lateral heterojunction architecture⁵

Access to surface electronic and chemical properties across channel

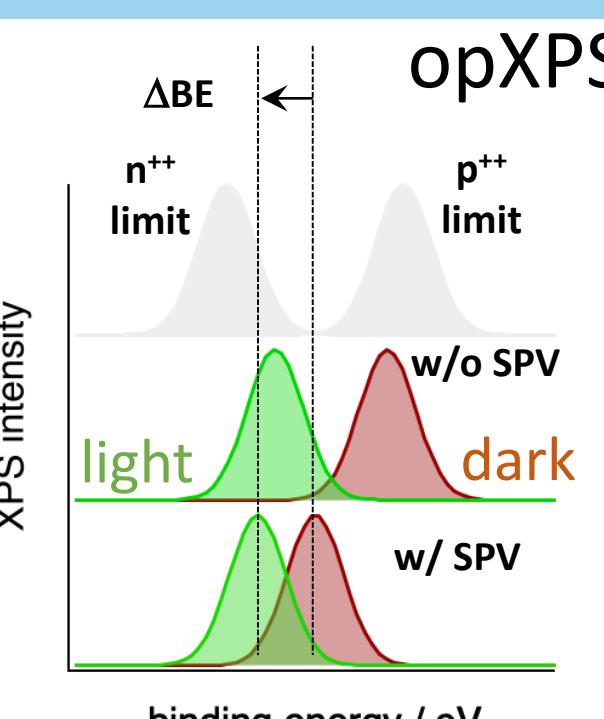
Photoelectron Spectroscopy across LHJ channel



- Lateral contact design as in interdigitated back contacts
- Perovskite deposition on top
- XPS/UPS data acquisition at end points
- Scanning PES (XPS, I 3d_{5/2}) across lateral heterojunction (LHJ)
- Drift-diffusion modelling to determine origin of surface potential^{5,6}
- Observed profile of surface potential requires low doping concentration in MHP (<10¹³ cm⁻³)

Conclusion and Next Steps

- Charge selective contacts shift the Fermi level in metal halide perovskites (MHPs)
- Effect is readily observable because of low defect and doping concentrations in the MHP
- Contact selectivity determines carrier extraction across MHP/contact interfaces
- Tailoring charge selective contacts to design MHP-based lateral heterojunction devices
- Operando measurements⁷ (opXPS & KPFM) to track dynamic effects and potential ion migration
- Access to buried interfaces via HAXPES measurements



References

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